

(19)



JAPANESE PATENT OFFICE

PATENT ABSTRACTS OF JAPAN

(11) Publication number: 2002026121 A

(43) Date of publication of application: 25.01.02

(51) Int. Cl

H01L 21/768

H01L 21/316

(21) Application number: 2000199737

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(22) Date of filing: 30.06.00

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(54) SEMICONDUCTOR DEVICE AND METHOD OF
MANUFACTURING THE SAME, AND METHOD
OF FORMING INSULATION FILM

(57) Abstract:

PROBLEM TO BE SOLVED: To increase the resistance with respect to various chemicals and plasma used in semiconductor manufacturing processes by improving the adhesiveness of a low-density film having low permittivity.

SOLUTION: The surface of the low-density film, having a low permittivity, is plasma-treated to form a very fine surface modified layer.

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